Central™
Semiconductor Corp.

PROCESS CPQ110

Triac

8.0 Amp, 600 Volt Triac Chip

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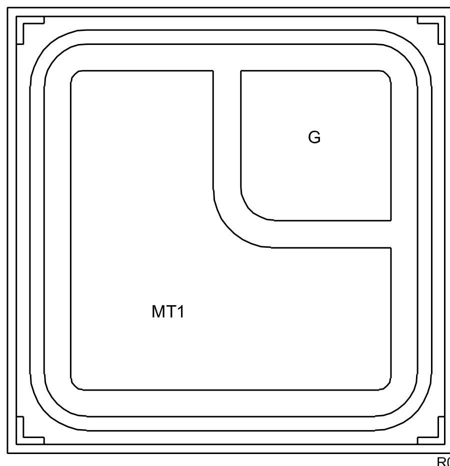
PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	110 MILS x 110 MILS
Die Thickness	8.6 MILS ± 0.6 MILS
MT1 Bonding Pad Area	80 MILS x 35 MILS
Gate Bonding Pad Area	37 MILS x 37 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Al/Mo/Ni/Ag - 32,000Å

GEOMETRY



BACKSIDE MT2

GROSS DIE PER 4 INCH WAFER
876

PRINCIPAL DEVICE TYPES
CQ220-8B Series
CQDD-8M Series

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